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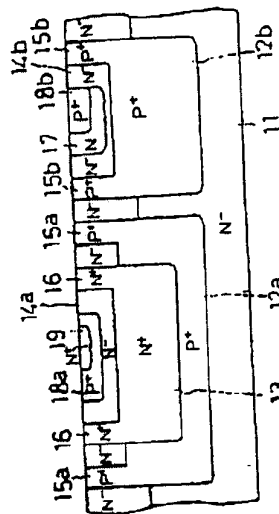
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TITLE : SEMICONDUCTOR INTEGRATED
CIRCUIT



ABSTRACT : PURPOSE: To dispense with a diffusion region used for isolating, to simplify a manufacturing process, and to lessen a chip in area by a method wherein the collector region and the collector lead-out region of a PNP transistor are made to serve also as an isolating region.

CONSTITUTION: An isolating region 12a of an NPN transistor and a collector region 12b of a PNP transistor are formed on an Si board 11, and a low resistive collector region 13 is formed in the region 12a. Then, a ring-shaped isolating region 15a and a ring-shaped collector lead-out region 15b are formed, and island regions 14a and 14b are formed. In succession, a collector electrode forming region 16 and a low resistive base region 17 are formed. At this point, a part of the region 14b is left unremoved between the region 17 and the collector lead-out region 15b. In succession, base regions 18a and 18b are formed at the same time, and then an emitter region 19 is formed inside a region 18a. By this setup, the regions 12a and the 15b are made to serve as the isolating region of a PNP transistor, so that a diffusion region used for isolation can be dispensed with, a manufacturing process is simplified, and a chip can be lessened in area.

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